





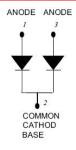
225CNQ015 SCHOTTKY RECTIFIER



Features

- 125°C T_J operation
- · Center tap module
- High purity, high temperature epoxy encapsulation for
- enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- · High current switching power supply
- Plating power supply
- Free-Wheeling diodes
- Reverse battery protection
- Converters
- UPS System
- Welding

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	15	V	
Average Rectified Forward Current	I _{F(AV)}	50% duty cycle @T _C =74°C, rectangular wave form	110(Per Leg)	A	
			220(Per Device)		
Peak One Cycle Non-Repetitive Surge Current (Per Leg)	I _{FSM}	8.3 ms, half Sine pulse	2040	Α	
Non-Repetitive Avalanche Energy(Peg Leg)	E _{AS}	TJ=25℃,I _{AS} =2A,L=4.5mH	9	mJ	
Repetitive Avalanche Current(Peg Leg)	I _{AR}	Current decaying linearly to zero in 1 µsec Frequency limited by T _J max. V _A =1.5×V _R typical	2	Α	

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V _{F1}	@ 110A, Pulse, T _J = 25 °C @ 220A, Pulse, T _J = 25 °C	0.35 -	0.38 0.49	V
	V _{F2}	@ 110A, Pulse, T _J = 125 °C @ 220A, Pulse, T _J = 125 °C	-	0.32 0.42	V
Reverse Current(Per Leg)*	I _{R1}	$@V_R = \text{rated } V_{R_1} T_J = 25 ^{\circ}\text{C}$	10	40	mA
	I _{R2}	$@V_R = \text{rated } V_{R_i} T_J = 125 ^{\circ}\text{C}$	-	2000	mA
	I _{R3}	@V _R =12V, T _J = 100 °C	800	1780	mA
	I _{R4}	@V _R = 5V, T _J = 100 °C	500	1080	mA
Junction Capacitance(Per leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	6600	7700	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

^{*} Pulse width < 300 µs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specific	cation	Units
Junction Temperature	TJ	-	-55 to +125		°C
Storage Temperature	T _{stg}	-	-55 to	+125	°C
Typical Thermal Resistance Junction to Case(Per leg)	R ₀ JC	DC operation	0.5	0	°C/W
Typical Thermal Resistance Junction to Case(Per package)	R _θ JC	DC operation	0.2	5	°C/W
Typical Thermal Resistance, case to Heat Sink	$R_{ heta cs}$	Mounting surface, smooth and greased	0.1	0	°C/W
Mounting Torque	т		Mounting Torque	24(min) 35(max)	Va om
Mounting Torque	T _M	-	Terminal Torque	35(min) 46(max)	- Kg-cm
Approximate Weight	wt	-	79)	g

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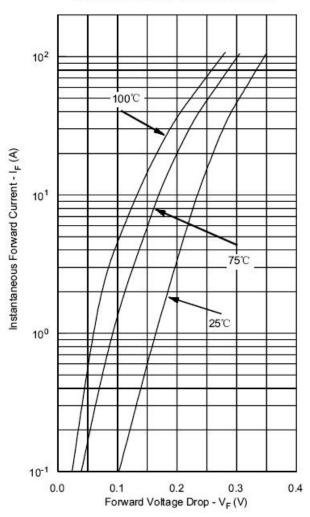




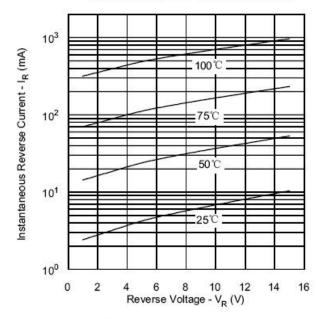


Ratings and Characteristics Curves

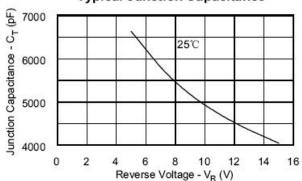
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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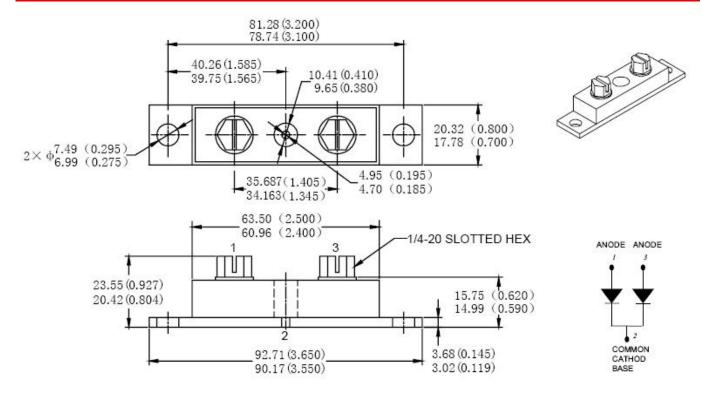
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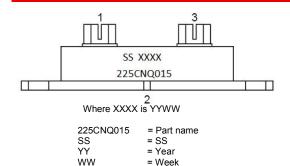




Mechanical Dimensions PRM4 Non-Isolated(Millimeters/Inches)



Marking Diagram



Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping	
225CNQ015	PRM4(Non- Isolated) (Pb-Free)	9 pcs/box	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.







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